

H. Föll: List of Publications

Second Installment: Running Number 61 - 120

Support

Below the fsecond installment of my publication list.

Links to: First installment (No. 1 - 60) Second installment (No. 61 -120) Third installment (No. 121 - 180) Fourth installment (No. 181 - 240) Fifth installment (No. 241 - 300) Sixth installment (No. 3001- 363)

60. [V. LEHMANN, V., FÖLL, H.](#): Formation mechanism and properties of electrochemically etched trenches in n-type silicon. J. Electrochem. Soc., 137 (1990) 653 **(1 133 citations)**
Nice way of staerting the list even so this paper was already on the preceding list.
61. [FÖLL, H., BECKER, F.S.](#): Industrielle Entwicklung und Fertigung von Halbleiterbauelementen. (Teil 1 und Teil 2, 80 Seiten, 38 Figuren), in: Festkörperforschung für die Informationstechnik (Hrsgb. und Vertrieb: KFA Jülich, Zentralbibliothek), Ferienkurs 1990, p. 16.1 (invited paper) [Part 2](#), [Part 3](#)
Very obscure reference ("Proceedings" of a summer school) but one of my major papers. One of the few papers (if not the only one) that describes in detail how a modern microelectronics chip is made.
62. KAKOSCHKE, R., BUßMANN, E., FÖLL, H.: Modelling of wafer heating during rapid thermal processing. Applied Physics, a50 (1990) 141 **(63 citations)**
63. FÖLL, H., LEHMANN, V., ZOTH, G., GELSDORF, F., GÖTTINGER, B.: In-line monitoring of heavy metal contaminations and interface states by an imaging technique. Proc. of the Satellite Symposium to ESSDERC '89 Berlin. (Analytical Technique for Semiconductor Material and Process Characterization) (eds.: B.O. Kolbesen, D.V.Mc Caughan, W. Wandervorst) Electrochem. Soc. Proc. Vol. 90-11 (1990) 44 (invited paper)
64. [BECKER, F.S., FÖLL, H., SCHLÜTER, K.](#): Die Mega-Generation. mc (Magazin für Computerpraxis) 12 (1990) 60 (invited paper)
65. FÖLL, H. WILD, B.: Polysilicon layers in modern microelectronic devices. Proc. POLYSE, Schwäbisch Hall 1990; (invited paper) Springer Proc. in Physics, Vol. 54 (Eds.: J.H. Werner und H.P. Strunk) p. 274 - 284
66. KAKOSCHKE, R., BUßMANN, E., FÖLL, H.: The appearance of temperature nonuniformities during rapid thermal processing. Appl. Phys. A 52 (1991) 52 **(26 citations)**
67. FÖLL, H.: Properties of silicon-electrolyte junctions and their application to silicon characterization. Appl. Phys. A 53 (1991) 8 - 19 **(236 citations)**
68. [BECKER, F.S., FÖLL, H.](#): Gigabit chips zur Jahrtausendwende?. Technische Rundschau 12 (1991) 26 - 32
69. [FÖLL, H., BECKER, F.S.](#): Megabit Speicher: Vom Projekt zum Produkt. Technische Rundschau 29 (1991) 44 - 51
70. FÖLL, H., KÜCHER, P.: Definition, Charakterisierung und Bewertung von Materialien der Mikroelektronik. In: Proc.2. Symposium Materialforschung, Dresden 1991, p. 3 (invited paper)
71. FÖLL, H.: Life time mapping with the ELYMAT technique. Proc. Symp. "Advanced Science and Technology of Si Materials", (Jap. Soc. Promotion of Science) Kona (Hawaii) 1991, p. 347 (invited paper)
72. FÖLL, H.: Challenges of 16 Mbit DRAM technology development. Proc.15th Nordic Semiconductor Meeting, (eds. S. Franssila, R. Daananen), VTT Semiconductor Laboratory; Hämeenlinna (Finnland) 1992, p. 115 (invited paper)
73. FÖLL, H.: Technological and economical aspects of mega-chip development. SET, Warszawa 1993, Electron Technology 26, 1 (1993) 23-34 (invited paper)
74. FÖLL, H., LEHMANN, V., LIPPIK, W.: Characterization of single and polycrystalline silicon by extension of the ELYMAT technique. Proc. of the Satellite Symp. to ESSDERC '93 Grenoble, "Crystalline Defects and Contamination: Their Impact and Control in Device Manufacturing", (ECS Proc. Vol. 93-15, 1993), p. 252
75. CARSTENSEN, J., LIPPIK, W., FÖLL, H.: Mapping of defect related bulk and surface properties with the ELYMAT technique. In Semiconductor Silicon/1994 (eds. H.R. Huff, W. Bergholz, K. Sumino),(ECS Proc. Vol. 94-10), San Francisco 1994, p. 1105 **(8 citations)**
76. CARSTENSEN, J., LIPPIK, W., FÖLL, H.: Mapping of defect related silicon properties with the ELYMAT technique in three dimensions. Proc. of "Semiconductor Processing and Characterization with Laser-Applications in Photovoltaics", Stuttgart 1994, Mat. Science Res. Forum Vols. 173-174, p.159
77. [GRÜNING, U., LEHMANN, V., OTTOW, S., BUSCH, K.](#): Macroporous silicon with a complete two dimensional

photonic band gap centered at 5 μm . J. Electrochem. Soc. (1995) (291 citations)

78. CARSTENSEN, J., LIPPIK, W., LIEBERT, S., KÖSTER, S., FÖLL, H.: New developments of the ELYMAT technique. Proc. of the Satellite Symp. to ESSDERC '95 Den Haag, "Analytical Techniques for Semiconductor Materials and Process Characterisation II", Electrochem. Soc. Proc. Vol. 95-30 (1995) 83-92
79. CARSTENSEN, J., LIPPIK, W., LIEBERT, S., KÖSTER, S., FÖLL, H.: ELYMAT technique on multicrystalline silicon for solar cell application.. Proc. of the "13th European Photovoltaic Conference and Exhibition", Nice, Okt. 1995, p. 1344-1347
80. OTTOW, S., LEHMANN, V., FÖLL, H.: Processing of three dimensional microstructures using macroporous n-type silicon. J. Electrochem. Soc. 143 (1996) , p. 385 (168 citations)
81. OTTOW, S., LEHMANN, V., FÖLL, H.: Development of three-dimensional microstructure processing using macroporous n-type silicon. Appl. Physics A 63 (1996), p. 153-159 (581 citations)
82. FÖLL, H.: Ingenieure für die Welt von morgen. (invited paper) Festschrift "25 Jahre VDI - Arbeitskreis Technik & Umwelt" (Hrsg. VDI Schleswig-Holsteinischer Bezirksverein), 1996, p. 24 - 28.
83. POPKIROV, G. S., OTTOW, S.: In situ impedance spectroscopy of silicon electrodes during the first stages of pore formation, Journal of Electroanalytical Chemistry, 429 (1997), 47-54 (13 citations)
I'm not an author but Ottow was a member of my team (Ph.D student)
84. Abschlußbericht zum Verbundprojekt: Verbesserung des Materialverständnisses von multikristallinem Silicium für Solarzellen: Defekte in kristallinem Silicium (DIXSI), Förderkennzeichen des BMBF 0329536A - I, p. 7-12 - 7-15, (1997)
85. BIRNER, A., GRÜNING, U., OTTOW, S., SCHNEIDER, A., MÜLLER, F., LEHMANN, V., FÖLL, H., GÖSELE, U.: Macroporous silicon: A two-dimensional photonic bandgap material suitable for the near-infrared spectral range, Physica Status Solidi (a), 165 (1)(1998) 111 (163 citations)
86. CARSTENSEN, J., PRANGE, R., POPKIROV, G. S., FÖLL, H.: A model of current oscillations at the Si-HF-system based on a quantitative analysis of current transients, Appl. Phys. A 67 (4) (1998) 459-467 (114 citations)
87. PRANGE, R., CARSTENSEN, J., FÖLL, H.: Transient current measurements on the Si-HF system as a direct image of the oxide thickness in the oscillation regime, in Proc. ECS' 193rd Meeting, San Diego 1998, 98-10, (1998) 158-170
88. CARSTENSEN, J., PRANGE, R., FÖLL, H.: Percolation model for the current oscillation in the Si-HF system, in Proc ECS' 193rd Meeting, San Diego 1998, 98-10, (1998) 148-157.
89. OTTOW, S., POPKIROV, G. S., FÖLL, H.: Determination of flat-band potentials of silicon electrodes in HF by means of a.c. resistance measurements, J. Electroanalytical Chemistry 455 (1998) 29-37 (44 citations)
90. FÖLL, H.: Multimedia in der Praxis. uni kiel 4 (1998) 1
91. CARSTENSEN, J., PRANGE, R., FÖLL, H.: A model for current-voltage oscillations at the Silicon electrode and comparison with experimental results, J. Electrochem. Soc. 146 (3), (1999) 1134-1140 (114 citations)
92. RÖNNEBECK, S., CARSTENSEN, J., OTTOW, S., FÖLL, H.: Crystal orientation dependence of macropore growth in n-type silicon, Electrochem. and Solid-State Letters 2 (3), (1999) 126 (115 citations)
93. LEHMANN, V., RÖNNEBECK, S.: The Physics of Macropore Formation in Low-Doped p-Type Silicon, J. Electrochem. Soc. 146 (8) (1999) 2968-2975 H. (115 citations)
I'm not an author but Silke Rönnebeck was a member of my team (Ph.D student)
94. AL-RIFAI, M., CARSTENSEN, J., FÖLL, H.: Improvement of the efficiency of silicon solar cells by electrochemical passivation of high leakage current areas in the pn-junction, in Proc. EUROMAT 1999, Volume 13 (Wiley-VCH) (1999) 273
95. JÄGER, C., DIECKER, C., JÄGER, W., CHRISTOPHERSEN, M., CARSTENSEN, J., FÖLL, H.: New insights into the formation of macropores in n-Si(001) and p-Si(001), in Proc. Microsc. Semicond. Mater. Conf. Oxford 1999, (Int. Phys. Conf. Ser. No. 164), (1999) 507-511
96. FÖLL, H.: Was heißt und zu welchem Ende studiert man Materialwissenschaft?. Forschungsbericht der CAU, Frühjahr 1999
97. JÄGER, C., FINKENBERGER, B., JÄGER, W., CHRISTOPHERSEN, M., CARSTENSEN, J., H. Föll: Transmission electron microscopy investigation of the formation of macropores in n- and p-Si(001)/(111), Mat. Sci. Eng. B 69-70 (2000) 199 (40 citations)
98. H. AL RIFAI, M., CHRISTOPHERSEN, M., OTTOW, S., CARSTENSEN, J., FÖLL, H.: Potential, temperature and doping dependence for macropore formation on n-Si with backside illumination, Journal of Porous Materials 7 (1/2/3)(2000) 33-36 H. (13 citations)
99. AL RIFAI, M., CHRISTOPHERSEN, M., OTTOW, S., CARSTENSEN, J., FÖLL, H.: Dependence of macropore formation in n-Si on potential, temperature, and doping, J. Electrochem. Soc. 147 (2)(2000) 627-635 (90 citations)
100. CARSTENSEN, J., CHRISTOPHERSEN, M., FÖLL, H.: Pore formation mechanisms for the Si-HF system, Mat. Sci. Eng. B 69-70 (2000) 23 (178 citations)
101. CHRISTOPHERSEN, M., CARSTENSEN, J., FEUERHAKE, A., FÖLL, H.: Crystal orientation and electrolyte dependence for macropore nucleation and stable growth on p-type-silicon, Mat. Sci. Eng. B 69-70 (2000) 194 (146 citations)
102. HASSE, G., CARSTENSEN, J., POPKIROV, G., FÖLL, H.: Current transient analysis of the oxidizing process in the complete anodic regime of the si-HF system, Mat. Sci. Eng. B 69-70 (2000) 188 (26 citations)
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103. CHRISTOPHERSEN, M., MERZ, P., QUENZER, J., CARSTENSEN, J., FÖLL, H.: A new method of silicon microstructuring with electrochemical etching, Phys. Stat. Sol. (a), 182 (1), (2000) 561 (18 citations)
104. FÖLL, H., CARSTENSEN, J., CHRISTOPHERSEN, M., HASSE, G.: A new view of silicon electrochemistry, (invited paper) Phys. Stat. Sol. (a), 182 (1), (2000) 7 (98 citations)
105. CHRISTOPHERSEN, M., CARSTENSEN, J., FÖLL, H.: Crystal orientation dependence of macropore formation of p- type silicon, Phys. Stat. Sol. (a), 182 (1), (2000) 103 (46 citations)
106. CHRISTOPHERSEN, M., CARSTENSEN, J., FÖLL, H.: Crystal orientation dependence of macropore formation of n-type silicon, Phys. Stat. Sol (a), 182 (2), (2000) 601 (18 citations)
107. CHRISTOPHERSEN, M., CARSTENSEN, J., FÖLL, H.: Macropore-formation on highly doped n-type silicon, Phys. Stat. Sol. (a), 182 (1), (2000) 45 (74 citations)
108. HASSE, G., CHRISTOPHERSEN, M., CARSTENSEN, J., FÖLL, H.: New insights into Si electrochemistry and pore growth by transient measurements and impedance spectroscopy, Phys. Stat. Sol. (a), 182 (1), (2000) 23 (23 citations)
109. CARSTENSEN, J., CHRISTOPHERSEN, M., HASSE, G., FÖLL, H.: Parameter dependence of pore formation in silicon within a model of local current bursts, Phys. Stat. Sol. (a) ,182 (1), (2000) 63 (98 citations)
110. J. CARSTENSEN, G. POPKIROV, J. BAHR, and H. FÖLL: CELLO: An advanced LBIC measurement for solarcell I local characterization, in Proceedings of the 16th European Photovoltaic Solar Energy Conference, Glasgow 2000, (2000) VD3.35 (162 citations)
111. LANGA, S., TIGINYANU, I. M., CARSTENSEN, J., CHRISTOPHERSEN, M., FÖLL, H.: Formation of porous layers with different morphologies during anodic etching of n-InP J. Electrochem. Soc. Lett. 3 (11), (2000) 514 (143 citations)
112. FÖLL, H., CARSTENSEN, J., CHRISTOPHERSEN, M., HASSE, G.: A stochastic model for current oscillations in space and time at the silicon electrode, in ECS Proceedings: Pits and Pores II: Formation Properties and Significance for Advanced Materials, 36 (2000) (9 citations)
113. HASSE, G, CARSTENSEN, J., and FÖLL, H.: Impedance Spectroscopy in the Si-HF system including time dependent and resonant phenomena, in ECS Proceedings: Pits and Pores II: Formation Properties and Significance for Advanced Materials, 531 (2000).
114. RÖNNEBECK, S., OTTOW, S., CARSTENSEN, J., FÖLL, H.: Crystal orientation dependence of macropore formation in n-Si with backside-illumination in HF-electrolyte. J. of Porous Mat. 7 (2000) 353-356 (best poster award) (21 citations)
115. MÜLLER, F., BIRNER, A., GÖSELE, U., LEHMANN, V., OTTOW, S., FÖLL, H.: Structuring of macroporous silicon for applications as photonic crystals. J. of Porous Mat. 7 (2000) 201-204 (best paper award) (117 citations)
116. FÖLL, H., FUCHS, F.W., JÄGER, W., PAUL, F.: New study courses in engineering at the university of Kiel. Proc. 3rd UICEE Annual Conf. on Engineering Education, Hobart, Australia, Feb. 2000, p. 163 - 166
117. PAUL, F., FÖLL, H., DOLGNER, K., JÄGER, W: New Masters Course Program in Materials Science and Engineering at the University of Kiel; 2000 SPRING MEETING PROCEEDINGS Symposium HH Materials Science and Engineering Education in the New Millenium Editors: B. London, E. Allen, A. Moll, D. Pope MRS Proceedings Volume 632
118. FÖLL, H.: Technologietransfer und Universität. hitecSH Forschung und Technologie in Schleswig-Holstein Jahrbuch (2000), p. 64-66
119. PAUL, F., FÖLL, H., JÄGER, W.: How to encourage young students to study engineering subjects. 4th UICEE Annual Conf. of Eng. Education, Singapore 2001
120. S. Langa, J. Carstensen, I. M. Tiginyanu, M. Christophersen, and H. Föll: Self-Induced Voltage Oscillations during Anodic Etching of n-InP and Possible Applications for Three-Dimensional Microstructures, Electrochemical and Solid-State Letters, 4 (6), G50-G52, (2001) (121 citations)

[Next installment \(No. 121 - 180\)](#)

Statistics

 Just for fun. The first table will yield my "Hirsch Factor" (look it up). The second table gives some idea of how one develops as an author. What defines "good journals" is not so clear. Here it is just my bias and must be seen as rather approximate.

No. citation	Inst. 1	Inst. 2	Inst. 3	Inst. 4	Inst. 5	Inst. 6	
>80	14	17					
>70							
>60		1					
>50	2						
>40	8	3					

	Inst. 1	Inst. 2	Inst. 3	Inst. 4	Inst. 5	Inst. 6	
First Author	35	17					
Good Journals	34	25					